

HYB25DC256803C[E/F]
HYB25DC256163C[E/F]

256-Mbit Double-Data-Rate SGRAM
Green Product

Datasheet Live

Internet Data Sheet

Rev. 1.30

HYB25DC256[80/16]3C[E/F]
256-Mbit Double-Data-Rate SGRAM

HYB25DC256803C[E/F], HYB25DC256163C[E/F]	
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Page	Subjects (major changes since last revision)
all	Adapted Internet Edition
all	Added new products
3	Added CL2.5 and CL2 to table 1
Previous Revision: 2007-01, Rev. 1.20	

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1 Overview

This chapter lists all main features of the product family 256-Mbit Double-Data-Rate SGRAM and the ordering information.

1.1 Features

- Double data rate architecture: two data transfers per clock cycle
- Bidirectional data strobe (DQS) is transmitted and received with data, to be used in capturing data at the receiver
- DQS is edge-aligned with data for reads and is center-aligned with data for writes
- Differential clock inputs (CK and $\overline{\text{CK}}$)
- Four internal banks for concurrent operation
- Data mask (DM) for write data
- DLL aligns DQ and DQS transitions with CK transitions
- Commands entered on each positive CK edge; data and data mask referenced to both edges of DQS
- Burst Lengths: 2, 4, or 8
- CAS Latency: 2, 2.5 or 3
- Auto Precharge option for each burst access
- Auto Refresh and Self Refresh Modes
- 7.8 μs Maximum Average Periodic Refresh Interval
- 2.5 V (SSTL_2 compatible) I/O
- $V_{\text{DDQ}} = 2.5 \text{ V} \pm 0.2 \text{ V}$ (DDR200, DDR266, DDR333); $V_{\text{DDQ}} = 2.6 \text{ V} \pm 0.1 \text{ V}$ (DDR400, DDR500)
- $V_{\text{DD}} = 2.5 \text{ V} \pm 0.2 \text{ V}$ (DDR200, DDR266, DDR333); $V_{\text{DD}} = 2.6 \text{ V} \pm 0.1 \text{ V}$ (DDR400, DDR500)
- PG-TSOP11-66 package
- PG-TFBGA-60 package
- Lead- and halogene-free = green product

TABLE 1
Performance

Part Number Speed Code			-4	-5	-6	Unit
Speed Grade			DDR500	DDR400B	DDR333	—
Max. Clock Frequency	@CL3	f_{CK3}	250	200	166	MHz
	@CL2.5	$f_{\text{CK2.5}}$	166	166	166	MHz
	@CL2	f_{CK2}	133	133	133	MHz

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1.2 Description

The 256-Mbit Double-Data-Rate SGRAM is a high-speed CMOS, dynamic random-access memory containing 268,435,456 bits. It is internally configured as a quad-bank DRAM.

The 256-Mbit Double-Data-Rate SGRAM uses a double-data-rate architecture to achieve high-speed operation. The double-data-rate architecture is essentially a 2n prefetch architecture with an interface designed to transfer two data words per clock cycle at the I/O pins. A single read or write access for the 256-Mbit Double-Data-Rate SGRAM effectively consists of a single 2n-bit wide, one clock cycle data transfer at the internal DRAM core and two corresponding n-bit wide, one-half-clock-cycle data transfers at the I/O pins.

A bidirectional data strobe (DQS) is transmitted externally, along with data, for use in data capture at the receiver. DQS is a strobe transmitted by the DDR SGRAM during Reads and by the memory controller during Writes. DQS is edge-aligned with data for Reads and center-aligned with data for Writes.

The 256-Mbit Double-Data-Rate SGRAM operates from a differential clock (CK and $\overline{\text{CK}}$; the crossing of CK going HIGH and $\overline{\text{CK}}$ going LOW is referred to as the positive edge of CK). Commands (address and control signals) are registered at every positive edge of CK. Input data is registered on both edges of DQS, and output data is referenced to both edges of DQS, as well as to both edges of CK. Read and write accesses to the DDR SGRAM are burst oriented; accesses start at a selected location and continue for a programmed number of locations in a programmed sequence. Accesses begin with the registration of an Active command, which is then followed by a Read or Write command. The address bits registered coincident with the Active command are used to select the bank and row to be accessed. The address bits registered coincident with the Read or Write command are used to select the bank and the starting column location for the burst access.

The DDR SGRAM provides for programmable Read or Write burst lengths of 2, 4 or 8 locations. An Auto Precharge function may be enabled to provide a self-timed row precharge that is initiated at the end of the burst access. As with standard SDRAMs, the pipelined, multibank architecture of DDR SGRAMs allows for concurrent operation, thereby providing high effective bandwidth by hiding row precharge and activation time.

An auto refresh mode is provided along with a power-saving power-down mode. All inputs are compatible with the Industry Standard for SSTL_2. All outputs are SSTL_2, Class II compatible.

Note: The functionality described and the timing specifications included in this data sheet are for the DLL Enabled mode of operation.

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256-Mbit Double-Data-Rate SGRAM**TABLE 2****Ordering Information for Lead free Products**

Product Type	Organisation	Clock (MHz)	Package	Note
HYB25DC256803CE-4	×8	250	PG-TSOPII-66	1)
HYB25DC256803CE-5		200		
HYB25DC256803CE-6		166		
HYB25DC256163CE-4	×16	250		
HYB25DC256163CE-5		200		
HYB25DC256163CE-6		166		
HYB25DC256803CF-4	×8	250	PG-TFBGA-60	1)
HYB25DC256803CF-5		200		
HYB25DC256803CF-6		166		
HYB25DC256163CF-4	×16	250		
HYB25DC256163CF-5		200		
HYB25DC256163CF-6		166		

1) RoHS Compliant Product: Restriction of the use of certain hazardous substances (RoHS) in electrical and electronic equipment as defined in the directive 2002/95/EC issued by the European Parliament and of the Council of 27 January 2003. These substances include mercury, lead, cadmium, hexavalent chromium, polybrominated biphenyls and polybrominated biphenyl ethers.

Note: Please check with your Qimonda representative that leadtime and availability of your preferred device type and version meet your project requirements.



2 Configuration

This chapter contains the chip configuration and block diagrams.

The chip configuration of a DDR SGRAM is listed by function in **Table 3**. The abbreviations used in the Buffer#Pin#/ column are explained in **Table 4** and **Table 5** respectively. The chip numbering for TSOP is depicted in **Figure 3**.

TABLE 3
Pin Configuration of DDR SDRAM

Ball#/Pin#	Name	Pin Type	Buffer Type	Function
Clock Signals				
G2, 45	CK	I	SSTL	Clock Signal
G3, 46	$\overline{\text{CK}}$	I	SSTL	Complementary Clock Signal
H3, 44	CKE	I	SSTL	Clock Enable
Control Signals				
H7, 23	$\overline{\text{RAS}}$	I	SSTL	Row Address Strobe
G8, 22	$\overline{\text{CAS}}$	I	SSTL	Column Address Strobe
G7, 21	$\overline{\text{WE}}$	I	SSTL	Write Enable
H8, 24	$\overline{\text{CS}}$	I	SSTL	Chip Select
Address Signals				
J8, 26	BA0	I	SSTL	Bank Address Bus 2:0
J7, 27	BA1	I	SSTL	
K7, 29	A0	I	SSTL	Address Bus 11:0
L8, 30	A1	I	SSTL	
L7, 31	A2	I	SSTL	
M8, 32	A3	I	SSTL	
M2, 35	A4	I	SSTL	
L3, 36	A5	I	SSTL	
L2, 37	A6	I	SSTL	
K3, 38	A7	I	SSTL	
K2, 39	A8	I	SSTL	
J3, 40	A9	I	SSTL	
K8, 28	A10	I	SSTL	
	AP	I	SSTL	
J2, 41	A11	I	SSTL	
H2, 42	A12	I	SSTL	Address Signal 12
	NC	NC	—	<i>Note: 128 Mbit or smaller dies</i>
F9, 17	A13	I	SSTL	Address Signal 13
	NC	NC	—	<i>Note: 1 Gbit based dies</i>
				<i>Note: 512 Mbit or smaller dies</i>



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Ball#/Pin#	Name	Pin Type	Buffer Type	Function
Data Signals ×8 organization				
A8, 2	DQ0	I/O	SSTL	Data Signal 7:0
B7, 5	DQ1	I/O	SSTL	
C7, 8	DQ2	I/O	SSTL	
D7, 11	DQ3	I/O	SSTL	
D3, 56	DQ4	I/O	SSTL	
C3, 59	DQ5	I/O	SSTL	
B3, 62	DQ6	I/O	SSTL	
A2, 65	DQ7	I/O	SSTL	
Data Strobe ×8 organisation				
E3, 51	DQS	I/O	SSTL	Data Strobe
Data Mask ×8 organization				
F3, 47	DM	I	SSTL	Data Mask
Data Signals ×16 organization				
A8, 2	DQ0	I/O	SSTL	Data Signal 15:0
B9, 4	DQ1	I/O	SSTL	
B7, 5	DQ2	I/O	SSTL	
C9, 7	DQ3	I/O	SSTL	
C7, 8	DQ4	I/O	SSTL	
D9, 10	DQ5	I/O	SSTL	
D7, 11	DQ6	I/O	SSTL	
E9, 13	DQ7	I/O	SSTL	
E1, 54	DQ8	I/O	SSTL	
D3, 56	DQ9	I/O	SSTL	
D1, 57	DQ10	I/O	SSTL	
C3, 59	DQ11	I/O	SSTL	
C1, 60	DQ12	I/O	SSTL	
B3, 62	DQ13	I/O	SSTL	
B1, 63	DQ14	I/O	SSTL	
A2, 65	DQ15	I/O	SSTL	
Data Strobe ×16 organization				
E3, 51	UDQS	I/O	SSTL	Data Strobe Upper Byte
E7, 16	LDQS	I/O	SSTL	Data Strobe Lower Byte
Data Mask ×16 organization				
F3, 47	UDM	I	SSTL	Data Mask Upper Byte
F7, 20	LDM	I	SSTL	Data Mask Lower Byte
Power Supplies				
F1, 49	V _{REF}	AI	—	I/O Reference Voltage
A9, B2, C8, D2, E8, 3, 9, 15, 55, 61	V _{DDQ}	PWR	—	I/O Driver Power Supply

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Ball#/Pin#	Name	Pin Type	Buffer Type	Function
A7, F8, M7, 1, 18, 33	V_{DD}	PWR	—	Power Supply
A1, B8, C2, D8, E2, 6, 12, 52, 58, 64	V_{SSQ}	PWR	—	Power Supply
A3, F2, M3, 34, 48, 66,	V_{SS}	PWR	—	Power Supply
Not Connected				
A2, A8, C3, C7, 2, 8, 59, 65	NC	NC	—	Not Connected
B1, B9, C1, C9, D1, D9, E1, E7, E9, F7, 4, 7, 10, 13, 16, 20, 54, 57, 60, 63	NC	NC	—	Not Connected <i>Note: $\times 8$ organisation</i>
F9, 14, 17, 19, 25, 43, 50, 53	NC	NC	—	Not Connected <i>Note: $\times 16, \times 8$ organization</i>

TABLE 4
Abbreviations for Pin Type

Abbreviation	Description
I	Standard input-only pin. Digital levels
O	Output. Digital levels
I/O	I/O is a bidirectional input/output signal
AI	Input. Analog levels
PWR	Power
GND	Ground
NC	Not Connected

TABLE 5
Abbreviations for Buffer Type

Abbreviation	Description
SSTL	Serial Stub Terminated Logic (SSTL2)
LV-CMOS	Low Voltage CMOS
CMOS	CMOS Levels
OD	Open Drain. The corresponding pin has 2 operational states, active low and tristate, and allows multiple devices to share as a wire-OR

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256-Mbit Double-Data-Rate SGRAM**FIGURE 1****Pin Configuration PG-TFBGA-60 (x8)Top View, see the balls through the package**

1	2	3	4	5	6	7	8	9
V_{SSQ}	DQ7	V_{SS}		A		V_{DD}	DQ0	V_{DDQ}
N.C.	V_{DDQ}	DQ6		B		DQ1	V_{SSQ}	N.C.
N.C.	V_{SSQ}	DQ5		C		DQ2	V_{DDQ}	N.C.
N.C.	V_{DDQ}	DQ4		D		DQ3	V_{SSQ}	N.C.
N.C.	V_{SSQ}	DQS		E		N.C.	V_{DDQ}	N.C.
V_{REF}	V_{SS}	DM		F		N.C.	V_{DD}	N.C.
	CK	\overline{CK}		G		\overline{WE}	\overline{CAS}	
	A12	CKE		H		\overline{RAS}	\overline{CS}	
	A11	A9		J		BA1	BA0	
	A8	A7		K		A0	A10/AP	
	A6	A5		L		A2	A1	
	A4	V_{SS}		M		V_{DD}	A3	
				x8				

MPPD0470

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256-Mbit Double-Data-Rate SGRAM**FIGURE 2****Pin Configuration PG-TFBGA-60 (x16)Top View, see the balls through the package**

1	2	3	4	5	6	7	8	9
V_{SSQ}	DQ15	V_{SS}		A		V_{DD}	DQ0	V_{DDQ}
DQ14	V_{DDQ}	DQ13		B		DQ2	V_{SSQ}	DQ1
DQ12	V_{SSQ}	DQ11		C		DQ4	V_{DDQ}	DQ3
DQ10	V_{DDQ}	DQ9		D		DQ6	V_{SSQ}	DQ5
DQ8	V_{SSQ}	UDQS		E		LDQS	V_{DDQ}	DQ7
V_{REF}	V_{SS}	UDM		F		LDM	V_{DD}	N.C.
	CK	\overline{CK}		G		\overline{WE}	\overline{CAS}	
	A12	CKE		H		\overline{RAS}	\overline{CS}	
	A11	A9		J		BA1	BA0	
	A8	A7		K		A0	A10/AP	
	A6	A5		L		A2	A1	
	A4	V_{SS}		M		V_{DD}	A3	

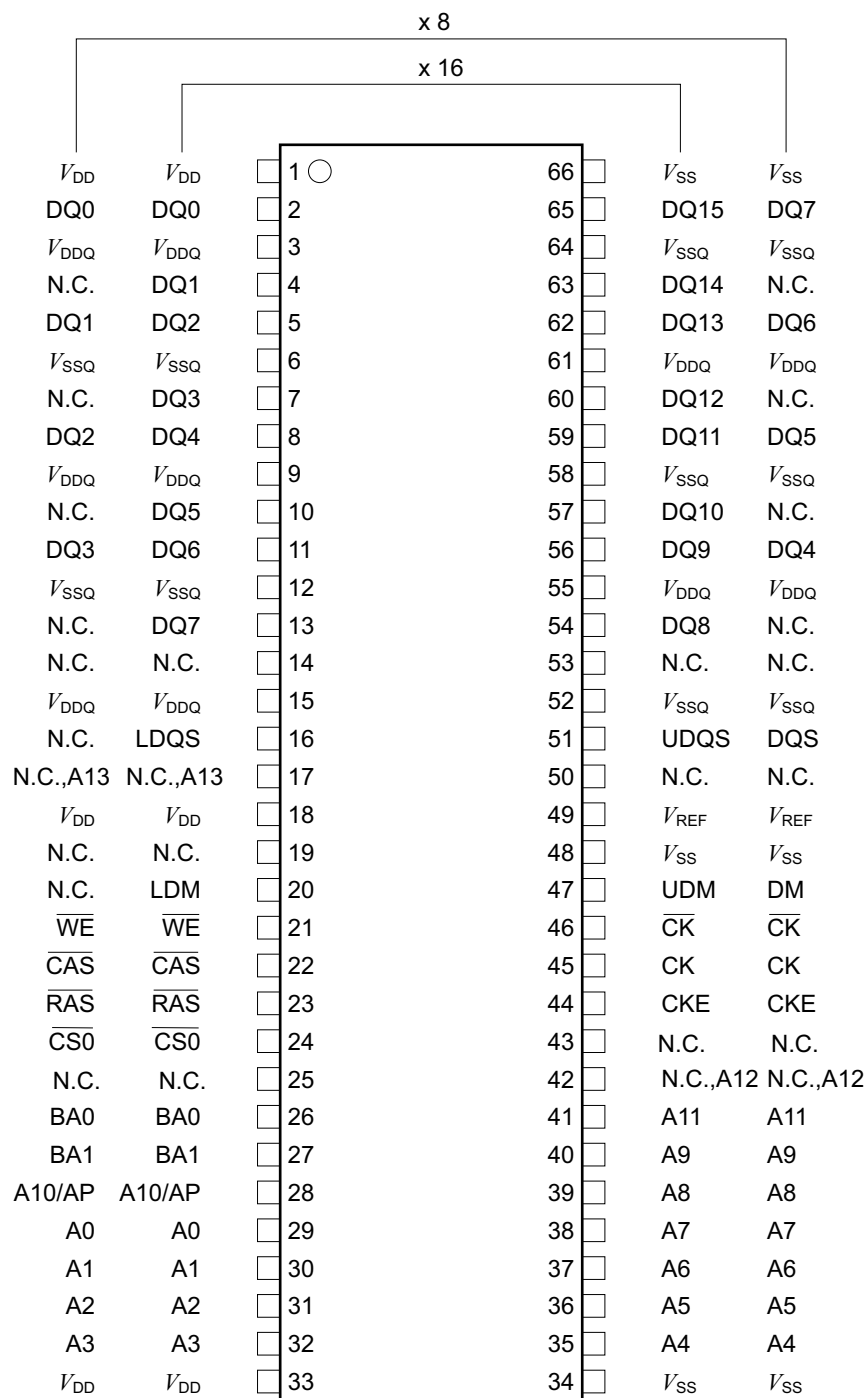
x16

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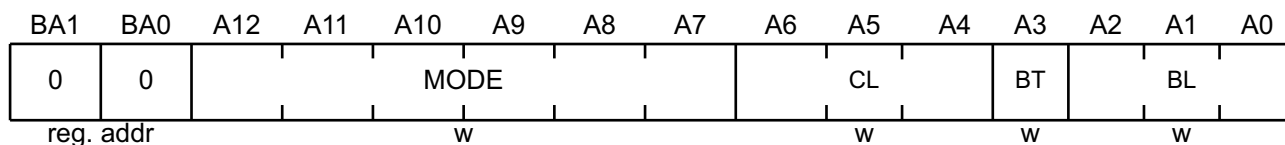
FIGURE 3
Chip Configuration PG-TSOP11-66



MPPD0450



3 Functional Description



MPBT0480

TABLE 6
Mode Register Definition

Field	Bits	Type ¹⁾	Description
BL	[2:0]	W	Burst Length Number of sequential bits per DQ related to one read/write command. <i>Note: All other bit combinations are RESERVED.</i> 001 _B 2 010 _B 4 011 _B 8
BT	3		Burst Type 0 Sequential 1 Interleaved
CL	[6:4]		CAS Latency Number of full clocks from read command to first data valid window. <i>Note: All other bit combinations are RESERVED.</i> 101 _B 1.5 010 _B 2 110 _B 2.5 011 _B 3 <i>Note: CL = 1.5 for DDR200 components only</i>
MODE	[12:7]		Operating Mode <i>Note: All other bit combinations are RESERVED.</i> 000000 Normal Operation without DLL Reset 000010 Normal Operation with DLL Reset

1) W = write only register bit

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Burst Definition

Burst Length	Starting Column Address			Order of Accesses Within a Burst	
	A2	A1	A0	Type = Sequential	Type = Interleaved
2			0	0-1	0-1
			1	1-0	1-0
4		0	0	0-1-2-3	0-1-2-3
		0	1	1-2-3-0	1-0-3-2
		1	0	2-3-0-1	2-3-0-1
		1	1	3-0-1-2	3-2-1-0
8	0	0	0	0-1-2-3-4-5-6-7	0-1-2-3-4-5-6-7
	0	0	1	1-2-3-4-5-6-7-0	1-0-3-2-5-4-7-6
	0	1	0	2-3-4-5-6-7-0-1	2-3-0-1-6-7-4-5
	0	1	1	3-4-5-6-7-0-1-2	3-2-1-0-7-6-5-4
	1	0	0	4-5-6-7-0-1-2-3	4-5-6-7-0-1-2-3
	1	0	1	5-6-7-0-1-2-3-4	5-4-7-6-1-0-3-2
	1	1	0	6-7-0-1-2-3-4-5	6-7-4-5-2-3-0-1
	1	1	1	7-0-1-2-3-4-5-6	7-6-5-4-3-2-1-0

Notes

1. For a burst length of two, A1-Ai selects the two-data-element block; A0 selects the first access within the block.
2. For a burst length of four, A2-Ai selects the four-data-element block; A0-A1 selects the first access within the block.
3. For a burst length of eight, A3-Ai selects the eight-data-element block; A0-A2 selects the first access within the block.
4. Whenever a boundary of the block is reached within a given sequence above, the following access wraps within the block.



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BA1	BA0	A12	A11	A10	A9	A8	A7	A6	A5	A4	A3	A2	A1	A0
0	1	OPERATING MODE											DS	DLL

MPBD2100

TABLE 8
Extended Mode Register

Field	Bits	Type ¹⁾	Description
DLL	0	W	DLL Status 0 _B Enabled 1 _B Disabled
DS	1		Drive Strength 0 _B Normal 1 _B Weak
MODE	[12:2]		Operating Mode <i>Note: All other bit combinations are RESERVED.</i> 00000000000 _B Normal Operation

1) W = write only register bit

HYB25DC256[80/16]3C[E/F]
256-Mbit Double-Data-Rate SGRAM**TABLE 9**
Truth Table 1a: Commands

Name (Function)	CS	RAS	CAS	WE	Address	MNE	Notes
Deselect (NOP)	H	X	X	X	X	NOP	1)2)
No Operation (NOP)	L	H	H	H	X	NOP	1)2)
Active (Select Bank And Activate Row)	L	L	H	H	Bank/Row	ACT	1)3)
Read (Select Bank And Column, And Start Read Burst)	L	H	L	H	Bank/Col	Read	1)4)
Write (Select Bank And Column, And Start Write Burst)	L	H	L	L	Bank/Col	Write	1)4)
Burst Terminate	L	H	H	L	X	BST	1)5)
Precharge (Deactivate Row In Bank Or Banks)	L	L	H	L	Code	PRE	1)6)
Auto Refresh Or Self Refresh (Enter Self Refresh Mode)	L	L	L	H	X	AR/SR	1)7)8)
Mode Register Set	L	L	L	L	Op-Code	MRS	1)9)

- 1) CKE is HIGH for all commands shown except Self Refresh. V_{REF} must be maintained during Self Refresh operation
- 2) Deselect and NOP are functionally interchangeable.
- 3) BA0-BA1 provide bank address and A0-Ai provide column address (where i = 9 for x8, i = 8 for x16).
- 4) BA0, BA1 provide bank address; A0-Ai provide column address (where i = 9 for x8, i = 8 for x16); A10 HIGH enables the Auto Precharge feature (nonpersistent), A10 LOW disables the Auto Precharge feature.
- 5) Applies only to read bursts with Auto Precharge disabled; this command is undefined (and should not be used) for read bursts with Auto Precharge enabled or for write bursts.
- 6) A10 LOW: BA0, BA1 determine which bank is precharged. A10 HIGH: all banks are precharged and BA0, BA1 are "Don't Care".
- 7) This command is Auto Refresh if CKE is HIGH; Self Refresh if CKE is LOW.
- 8) Internal refresh counter controls row and bank addressing; all inputs and I/Os are "Don't Care" except for CKE.
- 9) BA0, BA1 select either the Base or the Extended Mode Register (BA0 = 0, BA1 = 0 selects Mode Register; BA0 = 1, BA1 = 0 selects Extended Mode Register; other combinations of BA0-BA1 are reserved; A0-A12 provide the op-code to be written to the selected Mode Register).



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TABLE 10
Truth Table 1b: DM Operation

Name (Function)	DM	DQs	Note
Write Enable	L	Valid	1)
Write Inhibit	H	X	

1) Used to mask write data; provided coincident with the corresponding data.

TABLE 11
Truth Table 2: Clock Enable (CKE)

Current State	CKE n-1	CKEn	Command n	Action n	Note
	Previous Cycle	Current Cycle			
Self Refresh	L	L	X	Maintain Self-Refresh	1)
Self Refresh	L	H	Deselect or NOP	Exit Self-Refresh	2)
Power Down	L	L	X	Maintain Power-Down	—
Power Down	L	H	Deselect or NOP	Exit Power-Down	—
All Banks Idle	H	L	Deselect or NOP	Precharge Power-Down Entry	—
All Banks Idle	H	L	AUTO REFRESH	Self Refresh Entry	—
Bank(s) Active	H	L	Deselect or NOP	Active Power-Down Entry	—
	H	H	See Table 12	—	—

1) V_{REF} must be maintained during Self Refresh operation

2) Deselect or NOP commands should be issued on any clock edges occurring during the Self Refresh Exit (t_{XSNR}) period. A minimum of 200 clock cycles are needed before applying a read command to allow the DLL to lock to the input clock.

Notes

1. CKEn is the logic state of CKE at clock edge n; CKE n-1 was the state of CKE at the previous clock edge.
2. Current state is the state of the DDR SGRAM immediately prior to clock edge n.
3. COMMAND n is the command registered at clock edge n, and ACTION n is a result of COMMAND n.
4. All states and sequences not shown are illegal or reserved.

**TABLE 12****Truth Table 3: Current State Bank n - Command to Bank n (same bank)**

Current State	$\overline{\text{CS}}$	$\overline{\text{RAS}}$	$\overline{\text{CAS}}$	$\overline{\text{WE}}$	Command	Action	Note
Any	H	X	X	X	Deselect	NOP. Continue previous operation.	1)2)3)4)5)6)
	L	H	H	H	No Operation	NOP. Continue previous operation.	1) to 6)
Idle	L	L	H	H	Active	Select and activate row	1) to 6)
	L	L	L	H	AUTO REFRESH	–	1) to 7)
	L	L	L	L	MODE REGISTER SET	–	1) to 7)
Row Active	L	H	L	H	Read	Select column and start Read burst	1) to 6),8)
	L	H	L	L	Write	Select column and start Write burst	1) to 6),8)
	L	L	H	L	Precharge	Deactivate row in bank(s)	1) to 6),9)
Read (Auto Precharge Disabled)	L	H	L	H	Read	Select column and start new Read burst	1) to 6),8)
	L	L	H	L	Precharge	Truncate Read burst, start Precharge	1) to 6),9)
	L	H	H	L	BURST TERMINATE	BURST TERMINATE	1) to 6),10)
Write (Auto Precharge Disabled)	L	H	L	H	Read	Select column and start Read burst	1) to 6), 8),11)
	L	H	L	L	Write	Select column and start Write burst	1) to 6),8)
	L	L	H	L	Precharge	Truncate Write burst, start Precharge	1) to 6),9),11)

- 1) This table applies when CKE n-1 was HIGH and CKE n is HIGH (see [Table 11](#) and after $t_{\text{XSNR}}/t_{\text{XSRD}}$ has been met (if the previous state was self refresh).
- 2) This table is bank-specific, except where noted, i.e., the current state is for a specific bank and the commands shown are those allowed to be issued to that bank when in that state. Exceptions are covered in the notes below.
- 3) Current state definitions: Idle: The bank has been precharged, and t_{RP} has been met. Row Active: A row in the bank has been activated, and t_{RCD} has been met. No data bursts/accesses and no register accesses are in progress. Read: A Read burst has been initiated, with Auto Precharge disabled, and has not yet terminated or been terminated. Write: A Write burst has been initiated, with Auto Precharge disabled, and has not yet terminated or been terminated.
- 4) The following states must not be interrupted by a command issued to the same bank. Precharging: Starts with registration of a Precharge command and ends when t_{RP} is met. Once t_{RP} is met, the bank is in the idle state. Row Activating: Starts with registration of an Active command and ends when t_{RCD} is met. Once t_{RCD} is met, the bank is in the "row active" state. Read w/Auto Precharge Enabled: Starts with registration of a Read command with Auto Precharge enabled and ends when t_{RP} has been met. Once t_{RP} is met, the bank is in the idle state. Write w/Auto Precharge Enabled: Starts with registration of a Write command with Auto Precharge enabled and ends when t_{RP} has been met. Once t_{RP} is met, the bank is in the idle state. Deselect or NOP commands, or allowable commands to the other bank should be issued on any clock edge occurring during these states. Allowable commands to the other bank are determined by its current state and according to [Table 13](#).
- 5) The following states must not be interrupted by any executable command; Deselect or NOP commands must be applied on each positive clock edge during these states. Refreshing: Starts with registration of an Auto Refresh command and ends when t_{RFC} is met. Once t_{RFC} is met, the DDR SGRAM is in the "all banks idle" state. Accessing Mode Register: Starts with registration of a Mode Register Set command and ends when t_{MRD} has been met. Once t_{MRD} is met, the DDR SGRAM is in the "all banks idle" state. Precharging All: Starts with registration of a Precharge All command and ends when t_{RP} is met. Once t_{RP} is met, all banks is in the idle state.
- 6) All states and sequences not shown are illegal or reserved.
- 7) Not bank-specific; requires that all banks are idle.
- 8) Reads or Writes listed in the Command/Action column include Reads or Writes with Auto Precharge enabled and Reads or Writes with Auto Precharge disabled.
- 9) May or may not be bank-specific; if all/any banks are to be precharged, all/any must be in a valid state for precharging.
- 10) Not bank-specific; BURST TERMINATE affects the most recent Read burst, regardless of bank.
- 11) Requires appropriate DM masking.



TABLE 13

Truth Table 4: Current State Bank n - Command to Bank m (different bank)

Current State	$\overline{\text{CS}}$	$\overline{\text{RAS}}$	$\overline{\text{CAS}}$	$\overline{\text{WE}}$	Command	Action	Note
Any	H	X	X	X	Deselect	NOP. Continue previous operation.	1)2)3)4)5)6)
	L	H	H	H	No Operation	NOP. Continue previous operation.	1) to 6)
Idle	X	X	X	X	Any Command Otherwise Allowed to Bank m	–	1) to 6)
Row Activating, Active, or Precharging	L	L	H	H	Active	Select and activate row	1) to 6)
	L	H	L	H	Read	Select column and start Read burst	1) to 7)
	L	H	L	L	Write	Select column and start Write burst	1) to 7)
	L	L	H	L	Precharge	–	1) to 6)
Read (Auto Precharge Disabled)	L	L	H	H	Active	Select and activate row	1) to 6)
	L	H	L	H	Read	Select column and start new Read burst	1) to 7)
	L	L	H	L	Precharge	–	1) to 6)
Write (Auto Precharge Disabled)	L	L	H	H	Active	Select and activate row	1) to 6)
	L	H	L	H	Read	Select column and start Read burst	1) to 8)
	L	H	L	L	Write	Select column and start new Write burst	1) to 7)
	L	L	H	L	Precharge	–	1) to 6)
Read (With Auto Precharge)	L	L	H	H	Active	Select and activate row	1) to 6)
	L	H	L	H	Read	Select column and start new Read burst	1) to 7), 9)
	L	H	L	L	Write	Select column and start Write burst	1) to 7), 9), 10)
	L	L	H	L	Precharge	–	1) to 6)
Write (With Auto Precharge)	L	L	H	H	Active	Select and activate row	1) to 6)
	L	H	L	H	Read	Select column and start Read burst	1) to 7), 9)
	L	H	L	L	Write	Select column and start new Write burst	1) to 7), 9)
	L	L	H	L	Precharge	–	1) to 6)

- 1) This table applies when CKE n-1 was HIGH and CKE n is HIGH (see **Table 11**: Clock Enable (CKE) and after $t_{\text{XSNR}}/t_{\text{XSRD}}$ has been met (if the previous state was self refresh).
- 2) This table describes alternate bank operation, except where noted, i.e., the current state is for bank n and the commands shown are those allowed to be issued to bank m (assuming that bank m is in such a state that the given command is allowable). Exceptions are covered in the notes below.
- 3) Current state definitions: Idle: The bank has been precharged, and t_{RP} has been met. Row Active: A row in the bank has been activated, and t_{RCD} has been met. No data bursts/accesses and no register accesses are in progress. Read: A Read burst has been initiated, with Auto Precharge disabled, and has not yet terminated or been terminated. Write: A Write burst has been initiated, with Auto Precharge disabled, and has not yet terminated or been terminated. Read with Auto Precharge Enabled: See ¹⁰⁾. Write with Auto Precharge Enabled: See ¹⁰⁾.
- 4) AUTO REFRESH and Mode Register Set commands may only be issued when all banks are idle.
- 5) A BURST TERMINATE command cannot be issued to another bank; it applies to the bank represented by the current state only.
- 6) All states and sequences not shown are illegal or reserved.
- 7) Reads or Writes listed in the Command/Action column include Reads or Writes with Auto Precharge enabled and Reads or Writes with Auto Precharge disabled.
- 8) Requires appropriate DM masking.
- 9) **Concurrent Auto Precharge**: This device supports "Concurrent Auto Precharge". When a read with auto precharge or a write with auto precharge is enabled any command may follow to the other banks as long as that command does not interrupt the read or write data transfer and all other limitations apply (e.g. contention between READ data and WRITE data must be avoided). The minimum delay from a read or write command with auto precharge enable, to a command to a different banks is summarized in **Table 14**.

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10) A Write command may be applied after the completion of data output.

TABLE 14**Truth Table 5: Concurrent Auto Precharge**

From Command	To Command (different bank)	Minimum Delay with Concurrent Auto Precharge Support	Unit
WRITE w/AP	Read or Read w/AP	$1 + (BL/2) + t_{WTR}$	t_{CK}
	Write to Write w/AP	$BL/2$	t_{CK}
	Precharge or Activate	1	t_{CK}
Read w/AP	Read or Read w/AP	$BL/2$	t_{CK}
	Write or Write w/AP	$CL \text{ (rounded up)} + BL/2$	t_{CK}
	Precharge or Activate	1	t_{CK}



4 Electrical Characteristics

This chapter describes the electrical characteristics.

4.1 Operating Conditions

This chapter contains the operating conditions tables.

TABLE 15
Absolute Maximum Ratings

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Voltage on I/O pins relative to V_{SS}	V_{IN}, V_{OUT}	-0.5	—	$V_{DDQ} + 0.5$	V	—
Voltage on inputs relative to V_{SS}	V_{IN}	-1	—	+3.6	V	—
Voltage on V_{DD} supply relative to V_{SS}	V_{DD}	-1	—	+3.6	V	—
Voltage on V_{DDQ} supply relative to V_{SS}	V_{DDQ}	-1	—	+3.6	V	—
Operating temperature (ambient)	T_A	0	—	+70	°C	—
Storage temperature (plastic)	T_{STG}	-55	—	+150	°C	—
Power dissipation (per DDR SGRAM component)	P_D	—	1	—	W	—
Short circuit output current	I_{OUT}	—	50	—	mA	—

Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

TABLE 16
Input and Output Capacitances

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input Capacitance: CK, \overline{CK}	C_{I1}	2.0	—	3.0	pF	¹⁾
Delta Input Capacitance	C_{dl1}	—	—	0.25	pF	¹⁾
Input Capacitance: All other input-only pins	C_{I2}	2.0	—	3.0	pF	¹⁾
Delta Input Capacitance: All other input-only pins	C_{dlO}	—	—	0.5	pF	¹⁾
Input/Output Capacitance: DQ, DQS, DM	C_{IO}	4.0	—	5.0	pF	¹⁾²⁾
Delta Input/Output Capacitance: DQ, DQS, DM	C_{dlO}	—	—	0.5	pF	¹⁾

1) These values are guaranteed by design and are tested on a sample base only. $V_{DDQ} = V_{DD} = 2.5 \text{ V} \pm 0.2 \text{ V}$, $f = 100 \text{ MHz}$, $T_A = 25 \text{ °C}$, $V_{OUT(DC)} = V_{DDQ}/2$, V_{OUT} (Peak to Peak) 0.2 V. Unused pins are tied to ground.

2) DM inputs are grouped with I/O pins reflecting the fact that they are matched in loading to DQ and DQS to facilitate trace matching at the board level.



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TABLE 17
Electrical Characteristics and DC Operating Conditions

Parameter	Symbol	Values			Unit	Note/Test Condition ¹⁾
		Min.	Typ.	Max.		
Device Supply Voltage	V_{DD}	2.3	2.5	2.7	V	$f_{CK} \leq 166$ MHz
Device Supply Voltage	V_{DD}	2.5	2.6	2.7	V	$f_{CK} > 166$ MHz ²⁾
Output Supply Voltage	V_{DDQ}	2.3	2.5	2.7	V	$f_{CK} \leq 166$ MHz ³⁾
Output Supply Voltage	V_{DDQ}	2.5	2.6	2.7	V	$f_{CK} > 166$ MHz ²⁾³⁾
Supply Voltage, I/O Supply Voltage	V_{SS}, V_{SSQ}	0		0	V	—
Input Reference Voltage	V_{REF}	$0.49 \times V_{DDQ}$	$0.5 \times V_{DDQ}$	$0.51 \times V_{DDQ}$	V	⁴⁾
I/O Termination Voltage (System)	V_{TT}	$V_{REF} - 0.04$		$V_{REF} + 0.04$	V	⁵⁾
Input High (Logic1) Voltage	$V_{IH(DC)}$	$V_{REF} + 0.15$		$V_{DDQ} + 0.3$	V	⁶⁾
Input Low (Logic0) Voltage	$V_{IL(DC)}$	-0.3		$V_{REF} - 0.15$	V	⁶⁾
Input Voltage Level, CK and \overline{CK} Inputs	$V_{IN(DC)}$	-0.3		$V_{DDQ} + 0.3$	V	⁶⁾
Input Differential Voltage, CK and \overline{CK} Inputs	$V_{ID(DC)}$	0.36		$V_{DDQ} + 0.6$	V	⁶⁾⁷⁾
VI-Matching Pull-up Current to Pull-down Current	I_{Ratio}	0.71		1.4	—	⁸⁾
Input Leakage Current	I_I	-2		2	μA	Any input $0 V \leq V_{IN} \leq V_{DD}$; All other pins not under test = 0 V ⁹⁾
Output Leakage Current	I_{OZ}	-5		5	μA	DQs are disabled; $0 V \leq V_{OUT} \leq V_{DDQ}$ ⁹⁾
Output High Current, Normal Strength Driver	I_{OH}	—		-16.2	mA	$V_{OUT} = 1.95 V$
Output Low Current, Normal Strength Driver	I_{OL}	16.2		—	mA	$V_{OUT} = 0.35 V$

1) $0^\circ C \leq T_A \leq 70^\circ C$; $V_{DDQ} = 2.5 V \pm 0.2 V$, $V_{DD} = +2.5 V \pm 0.2 V$;

2) DDR400 conditions apply for all clock frequencies above 166 MHz

3) Under all conditions, V_{DDQ} must be less than or equal to V_{DD} .

4) Peak to peak AC noise on V_{REF} may not exceed $\pm 2\%$ $V_{REF,DC}$. V_{REF} is also expected to track noise variations in V_{DDQ} .

5) V_{TT} is not applied directly to the device. V_{TT} is a system supply for signal termination resistors, is expected to be set equal to V_{REF} , and must track variations in the DC level of V_{REF} .

6) Inputs are not recognized as valid until V_{REF} stabilizes.

7) V_{ID} is the magnitude of the difference between the input level on CK and the input level on \overline{CK} .

8) The ratio of the pull-up current to the pull-down current is specified for the same temperature and voltage, over the entire temperature and voltage range, for device drain to source voltage from 0.25 to 1.0 V. For a given output, it represents the maximum difference between pull-up and pull-down drivers due to process variation.

9) Values are shown per pin.

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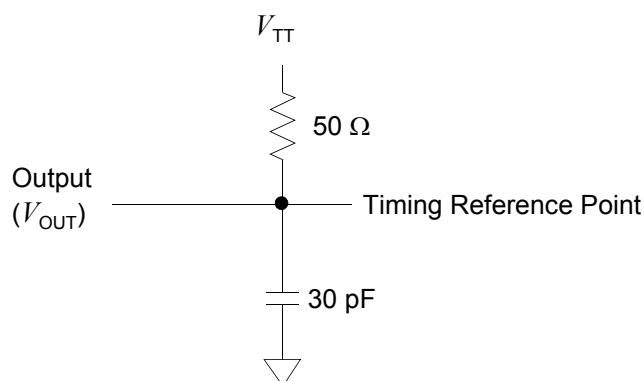
4.2 AC Characteristics

(Notes 1-5 apply to the following Tables; Electrical Characteristics and DC Operating Conditions, AC Operating Conditions, I_{DD} Specifications and Conditions, and Electrical Characteristics and AC Timing.)

Notes

1. All voltages referenced to V_{SS} .
2. Tests for AC timing, I_{DD} , and electrical, AC and DC characteristics, may be conducted at nominal reference/supply voltage levels, but the related specifications and device operation are guaranteed for the full voltage range specified.
3. **Figure 4** represents the timing reference load used in defining the relevant timing parameters of the part. It is not intended to be either a precise representation of the typical system environment nor a depiction of the actual load presented by a production tester. System designers will use IBIS or other simulation tools to correlate the timing reference load to a system environment. Manufacturers will correlate to their production test conditions (generally a coaxial transmission line terminated at the tester electronics).
4. AC timing and I_{DD} tests may use a V_{IL} to V_{IH} swing of up to 1.5 V in the test environment, but input timing is still referenced to V_{REF} (or to the crossing point for CK, \overline{CK}), and parameter specifications are guaranteed for the specified AC input levels under normal use conditions. The minimum slew rate for the input signals is 1 V/ns in the range between $V_{IL(AC)}$ and $V_{IH(AC)}$.
5. The AC and DC input level specifications are as defined in the SSTL_2 Standard (i.e. the receiver effectively switches as a result of the signal crossing the AC input level, and remains in that state as long as the signal does not ring back above (below) the DC input LOW (HIGH) level).
6. For System Characteristics like Setup & Holdtime Derating for Slew Rate, I/O Delta Rise/Fall Derating, DDR SGRAM Slew Rate Standards, Overshoot & Undershoot specification and Clamp V - I characteristics see the latest Industry specification for DDR components.

FIGURE 4
AC Output Load Circuit Diagram / Timing Reference Load





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TABLE 18
AC Operating Conditions

Parameter	Symbol	Values		Unit	Note/ Test Condition
		Min.	Max.		
Input High (Logic 1) Voltage, DQ, DQS and DM Signals	$V_{IH(AC)}$	$V_{REF} + 0.31$	—	V	1)2)3)
Input Low (Logic 0) Voltage, DQ, DQS and DM Signals	$V_{IL(AC)}$	—	$V_{REF} - 0.31$	V	1)2)3)
Input Differential Voltage, CK and \overline{CK} Inputs	$V_{ID(AC)}$	0.7	$V_{DDQ} + 0.6$	V	1)2)3)4)
Input Closing Point Voltage, CK and \overline{CK} Inputs	$V_{IX(AC)}$	$0.5 \times V_{DDQ} - 0.2$	$0.5 \times V_{DDQ} + 0.2$	V	1)2)3)5)

- 1) $V_{DDQ} = 2.5\text{ V} \pm 0.2\text{ V}$, $V_{DD} = +2.5\text{ V} \pm 0.2\text{ V}$ (DDR200 - DDR333); $V_{DDQ} = 2.6\text{ V} \pm 0.1\text{ V}$, $V_{DD} = +2.6\text{ V} \pm 0.1\text{ V}$ (DDR400); $0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$
2) Input slew rate = 1 V/ns.
3) Inputs are not recognized as valid until V_{REF} stabilizes.
4) V_{ID} is the magnitude of the difference between the input level on CK and the input level on \overline{CK} .
5) The value of V_{IX} is expected to equal $0.5 \times V_{DDQ}$ of the transmitting device and must track variations in the DC level of the same.

TABLE 19
AC Timing - Absolute Specifications

Parameter	Symbol	−4		−5		−6		Unit	Note/ Test Condition ¹⁾
		DDR500		DDR400B		DDR333			
		Min.	Max.	Min.	Max.	Min.	Max.		
DQ output access time from CK/ \overline{CK}	t_{AC}	−0.5	+0.5	−0.5	+0.5	−0.7	+0.7	ns	2)3)4)5)
CK high-level width	t_{CH}	0.45	0.55	0.45	0.55	0.45	0.55	t_{CK}	2)3)4)5)
Clock cycle time	t_{CK}	4	12	5	7.5	6	12	ns	CL = 3.0 2)3)4)5)
CK low-level width	t_{CL}	0.45	0.55	0.45	0.55	0.45	0.55	t_{CK}	2)3)4)5)
Auto precharge write recovery + precharge time	t_{DAL}	$(t_{WR}/t_{CK})+(t_{RP}/t_{CK})$						t_{CK}	2)3)4)5)6)
DQ and DM input hold time	t_{DH}	0.4	—	0.4	—	0.45	—	ns	2)3)4)5)
DQ and DM input pulse width (each input)	t_{DIPW}	1.75	—	1.75	—	1.75	—	ns	2)3)4)5)6)
DQS output access time from CK/ \overline{CK}	t_{DQSCK}	−0.6	+0.6	−0.6	+0.6	−0.6	+0.6	ns	2)3)4)5)
DQS input low (high) pulse width (write cycle)	$t_{DQSL,H}$	0.35	—	0.35	—	0.35	—	t_{CK}	2)3)4)5)
DQS-DQ skew (DQS and associated DQ signals)	t_{DQSQ}	—	0.5	—	0.4	—	0.45	ns	TSOPII 2)3)4)5)



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Parameter	Symbol	–4		–5		–6		Unit	Note/ Test Condition ¹⁾
		DDR500		DDR400B		DDR333			
		Min.	Max.	Min.	Max.	Min.	Max.		
DQS-DQ skew (DQS and associated DQ signals)	t_{DQSQ}	—	0.4	—	0.4	—	0.4	ns	TFBGA 2)3)4)5)
Write command to 1 st DQS latching transition	t_{DQSS}	0.72	1.15	0.72	1.25	0.75	1.25	t_{CK}	2)3)4)5)
DQ and DM input setup time	t_{DS}	0.4	—	0.4	—	0.45	—	ns	2)3)4)5)
DQS falling edge hold time from CK (write cycle)	t_{DSH}	0.2	—	0.2	—	0.2	—	t_{CK}	2)3)4)5)
DQS falling edge to CK setup time (write cycle)	t_{DSS}	0.2	—	0.2	—	0.2	—	t_{CK}	2)3)4)5)
Clock Half Period	t_{HP}	min. (t_{CL} , t_{CH})	—	min. (t_{CL} , t_{CH})	—	min. (t_{CL} , t_{CH})	—	ns	2)3)4)5)
Data-out high-impedance time from CK/ \overline{CK}	t_{HZ}	—	+0.7	—	+0.7	—	+0.7	ns	2)3)4)5)7)
Address and control input hold time	t_{IH}	0.6	—	0.6	—	0.75	—	ns	fast slew rate 3)4)5)6)8)
		0.7	—	0.7	—	0.8	—	ns	slow slew rate ³⁾⁴⁾⁵⁾⁶⁾⁸⁾
Control and Addr. input pulse width (each input)	t_{IPW}	2.2	—	2.2	—	2.2	—	ns	2)3)4)5)9)
Address and control input setup time	t_{IS}	0.6	—	0.6	—	0.75	—	ns	fast slew rate 3)4)5)6)8)
		0.7	—	0.7	—	0.8	—	ns	slow slew rate ³⁾⁴⁾⁵⁾⁶⁾⁸⁾
Data-out low-impedance time from CK/ \overline{CK}	t_{LZ}	–0.7	+0.7	–0.7	+0.7	–0.7	+0.7	ns	2)3)4)5)7)
Mode register set command cycle time	t_{MRD}	2	—	2	—	2	—	t_{CK}	2)3)4)5)
DQ/DQS output hold time from DQS	t_{QH}	$t_{HP} - t_{QHS}$	—	$t_{HP} - t_{QHS}$	—	$t_{HP} - t_{QHS}$	—	ns	2)3)4)5)
Data hold skew factor	t_{QHS}	—	0.4	—	0.5	—	0.55	ns	TSOPII ²⁾³⁾⁴⁾⁵⁾
Data hold skew factor	t_{QHS}	—	0.5	—	0.5	—	0.5	ns	TFBGA 2)3)4)5)

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Parameter	Symbol	−4		−5		−6		Unit	Note/ Test Condition ¹⁾
		DDR500		DDR400B		DDR333			
		Min.	Max.	Min.	Max.	Min.	Max.		
Active to Autoprecharge delay	<i>t</i> _{RAP}	<i>t</i> _{RCD}	—	<i>t</i> _{RCD}	—	<i>t</i> _{RCD}	—	ns	2)3)4)5)
Active to Precharge command	<i>t</i> _{RAS}	36	70E+3	40	70E+3	42	70E+3	ns	2)3)4)5)
Active to Active/Auto-refresh command period	<i>t</i> _{RC}	52	—	55	—	60	—	ns	2)3)4)5)
Active to Write or Read delay	<i>t</i> _{RCDWR}	12	—	15	—	18	—	ns	2)3)4)5)
Average Periodic Refresh Interval	<i>t</i> _{REFI}	—	7.8	—	7.8	—	7.8	μs	2)3)4)5)8)
Auto-refresh to Active/Auto-refresh command period	<i>t</i> _{RFC}	60	—	65	—	72	—	ns	2)3)4)5)
Precharge command period	<i>t</i> _{RP}	12	—	15	—	18	—	ns	2)3)4)5)
Read preamble	<i>t</i> _{RPRE}	0.9	1.1	0.9	1.1	0.9	1.1	<i>t</i> _{CK}	2)3)4)5)
Read postamble	<i>t</i> _{RPST}	0.4	0.6	0.4	0.6	0.4	0.6	<i>t</i> _{CK}	2)3)4)5)
Active bank A to Active bank B command	<i>t</i> _{RRD}	8	—	10	—	12	—	ns	2)3)4)5)
Write preamble	<i>t</i> _{WPRE}	0.25	—	0.25	—	0.25	—	<i>t</i> _{CK}	2)3)4)5)
Write preamble setup time	<i>t</i> _{WPRES}	0	—	0	—	0	—	ns	2)3)4)5)10)
Write postamble	<i>t</i> _{WPST}	0.4	0.6	0.4	0.6	0.4	0.6	<i>t</i> _{CK}	2)3)4)5)11)
Write recovery time	<i>t</i> _{WR}	15	—	15	—	15	—	ns	2)3)4)5)
Internal write to read command delay	<i>t</i> _{WTR}	1	—	1	—	1	—	<i>t</i> _{CK}	2)3)4)5)
Exit self-refresh to non-read command	<i>t</i> _{XSNR}	75	—	75	—	75	—	ns	2)3)4)5)
Exit self-refresh to read command	<i>t</i> _{XSRD}	200	—	200	—	200	—	<i>t</i> _{CK}	2)3)4)5)

1) $0^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$; $V_{DDQ} = 2.5\text{ V} \pm 0.2\text{ V}$, $V_{DD} = +2.5\text{ V} \pm 0.2\text{ V}$ (DDR333); $V_{DDQ} = 2.6\text{ V} \pm 0.1\text{ V}$, $V_{DD} = +2.6\text{ V} \pm 0.1\text{ V}$ (DDR400)

2) Input slew rate $\geq 1\text{ V/ns}$ for DDR400, DDR333

3) The CK/CK input reference level (for timing reference to CK/CK) is the point at which CK and CK cross: the input reference level for signals other than CK/CK, is V_{REF} . CK/CK slew rate are $\geq 1.0\text{ V/ns}$.

4) Inputs are not recognized as valid until V_{REF} stabilizes.

5) The Output timing reference level, as measured at the timing reference point indicated in AC Characteristics (note 3) is V_{TT} .

6) For each of the terms, if not already an integer, round to the next highest integer. t_{CK} is equal to the actual system clock cycle time.

7) t_{HZ} and t_{LZ} transitions occur in the same access time windows as valid data transitions. These parameters are not referred to a specific voltage level, but specify when the device is no longer driving (HZ), or begins driving (LZ).



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- 8) Fast slew rate ≥ 1.0 V/ns, slow slew rate ≥ 0.5 V/ns and < 1 V/ns for command/address and CK & $\overline{\text{CK}}$ slew rate > 1.0 V/ns, measured between $V_{\text{IH(ac)}}$ and $V_{\text{IL(ac)}}$.
- 9) These parameters guarantee device timing, but they are not necessarily tested on each device.
- 10) The specific requirement is that DQS be valid (HIGH, LOW, or some point on a valid transition) on or before this CK edge. A valid transition is defined as monotonic and meeting the input slew rate specifications of the device. When no writes were previously in progress on the bus, DQS will be transitioning from Hi-Z to logic LOW. If a previous write was in progress, DQS could be HIGH, LOW at this time, depending on t_{DQSS} .
- 11) The maximum limit for this parameter is not a device limit. The device operates with a greater value for this parameter, but system performance (bus turnaround) degrades accordingly.

TABLE 20
 I_{DD} Conditions

Parameter	Symbol
Operating Current: one bank; active/ precharge; $t_{\text{RC}} = t_{\text{RCMIN}}$; $t_{\text{CK}} = t_{\text{CKMIN}}$; DQ, DM, and DQS inputs changing once per clock cycle; address and control inputs changing once every two clock cycles.	I_{DD0}
Operating Current: one bank; active/read/precharge; Burst = 4; Refer to the following page for detailed test conditions.	I_{DD1}
Precharge Power-Down Standby Current: all banks idle; power-down mode; $\text{CKE} \leq V_{\text{ILMAX}}$; $t_{\text{CK}} = t_{\text{CKMIN}}$	I_{DD2P}
Precharge Floating Standby Current: $\overline{\text{CS}} \geq V_{\text{IHMIN}}$, all banks idle; $\text{CKE} \geq V_{\text{IHMIN}}$; $t_{\text{CK}} = t_{\text{CKMIN}}$, address and other control inputs changing once per clock cycle, $V_{\text{IN}} = V_{\text{REF}}$ for DQ, DQS and DM.	I_{DD2F}
Precharge Quiet Standby Current: $\overline{\text{CS}} \geq V_{\text{IHMIN}}$, all banks idle; $\text{CKE} \geq V_{\text{IHMIN}}$; $t_{\text{CK}} = t_{\text{CKMIN}}$, address and other control inputs stable at $\geq V_{\text{IHMIN}}$ or $\leq V_{\text{ILMAX}}$; $V_{\text{IN}} = V_{\text{REF}}$ for DQ, DQS and DM.	I_{DD2Q}
Active Power-Down Standby Current: one bank active; power-down mode; $\text{CKE} \leq V_{\text{ILMAX}}$; $t_{\text{CK}} = t_{\text{CKMIN}}$; $V_{\text{IN}} = V_{\text{REF}}$ for DQ, DQS and DM.	I_{DD3P}
Active Standby Current: one bank active; $\overline{\text{CS}} \geq V_{\text{IHMIN}}$; $\text{CKE} \geq V_{\text{IHMIN}}$; $t_{\text{RC}} = t_{\text{RASMAX}}$; $t_{\text{CK}} = t_{\text{CKMIN}}$; DQ, DM and DQS inputs changing twice per clock cycle; address and control inputs changing once per clock cycle	I_{DD3N}
Operating Current: one bank active; Burst = 2; reads; continuous burst; address and control inputs changing once per clock cycle; 50% of data outputs changing on every clock edge; CL = 2 for DDR200 and DDR266A, CL = 3 for DDR333; $t_{\text{CK}} = t_{\text{CKMIN}}$; $I_{\text{OUT}} = 0$ mA	I_{DD4R}
Operating Current: one bank active; Burst = 2; writes; continuous burst; address and control inputs changing once per clock cycle; 50% of data outputs changing on every clock edge; CL = 2 for DDR200 and DDR266A, CL = 3 for DDR333; $t_{\text{CK}} = t_{\text{CKMIN}}$	I_{DD4W}
Auto-Refresh Current: $t_{\text{RC}} = t_{\text{RFCMIN}}$, burst refresh	I_{DD5}
Self-Refresh Current: $\text{CKE} \leq 0.2$ V; external clock on; $t_{\text{CK}} = t_{\text{CKMIN}}$	I_{DD6}
Operating Current: four bank; four bank interleaving with BL = 4; Refer to the following page for detailed test conditions.	I_{DD7}

HYB25DC256[80/16]3C[E/F]
256-Mbit Double-Data-Rate SGRAM**TABLE 21** **I_{DD} Specification**

Symbol	–4	–5	–6	Unit	Note/Test Condition ¹⁾
I_{DD0}	115	75	65	mA	2)3)
I_{DD1}	135	95	80	mA	3)
I_{DD2P}	6	4	4	mA	3)
I_{DD2F}	45	30	25	mA	3)
I_{DD2Q}	35	20	17	mA	3)
I_{DD3P}	23	13	11	mA	3)
I_{DD3N}	65	43	36	mA	3)
I_{DD4R}	150	100	85	mA	3)
I_{DD4W}	160	100	90	mA	3)
I_{DD5}	240	140	120	mA	3)
I_{DD6}	2.8	1.4	1.4	mA	4)
I_{DD7}	315	210	180	mA	3)

1) Test conditions: $V_{DD} = 2.7\text{ V}$, $T_A = 10\text{ °C}$ 2) I_{DD} specifications are tested after the device is properly initialized and measured at 133 MHz for DDR266, 166 MHz for DDR333, and 200 MHz for DDR400, 250MHz for DDR500

3) Input slew rate = 1 V/ns.

4) Enables on-chip refresh and address counters.

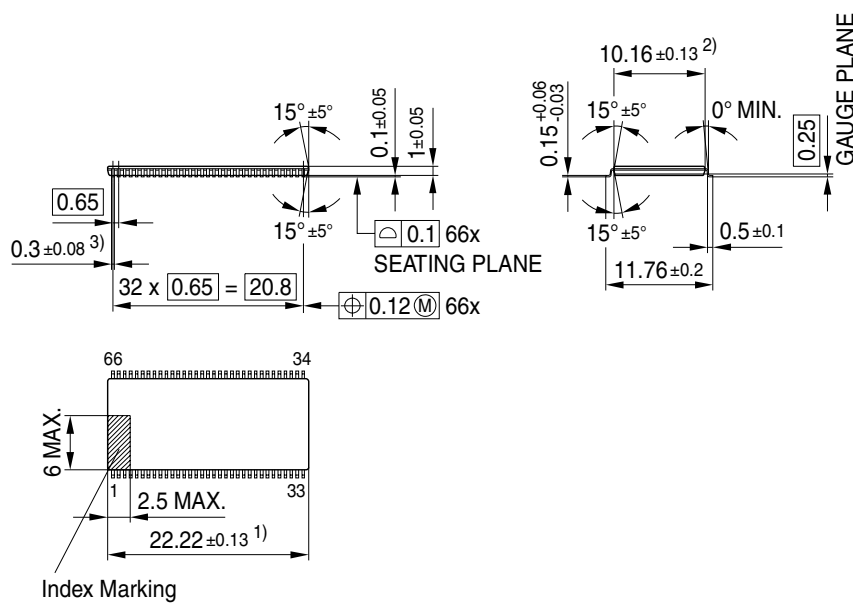


HYB25DC256[80/16]3C[E/F]
256-Mbit Double-Data-Rate SGRAM

5 Package Outlines

There are two package types used for this product family: TSOP and TFBGA.

FIGURE 5
Package Outline PG-TSOPII-66



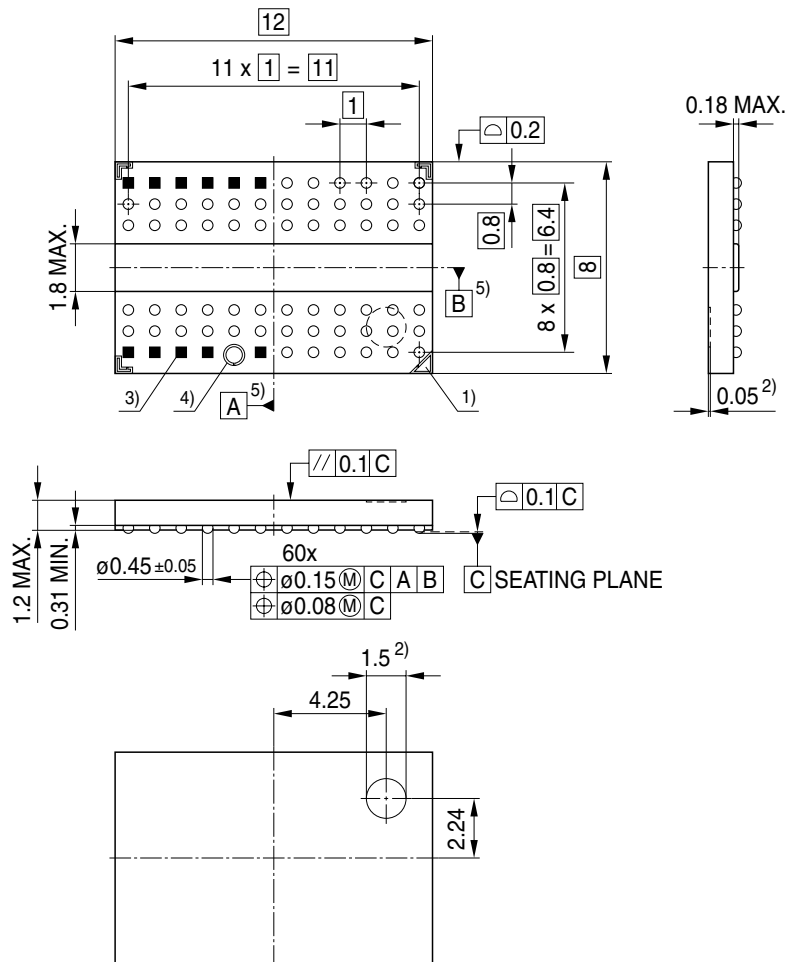
- 1) Does not include plastic or metal protrusion of 0.15 max. per side
2) Does not include plastic protrusion of 0.25 max. per side
3) Does not include dambar protrusion of 0.13 max.

FPO_P_-TSOPII_-066-001



HYB25DC256[80/16]3C[E/F]
256-Mbit Double-Data-Rate SGRAM

FIGURE 6
Package Outline of PG-TFBGA-60



Lead-free (green) solder balls

- 1) A1 marking ballside
- 2) A1 marking chipside
- 3) Dummy pads without ball ■
- 4) Bad unit marking (BUM)
- 5) Middle of packages edges

FPO_PG-TFBGA__-060-019

Notes

- 1. Drawing according to ISO 8015
- 2. Dimensions in mm
- 3. General tolerances +/- 0.15



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